

**BCX70 SERIES**  
**SURFACE MOUNT**  
**NPN SILICON TRANSISTOR**



[www.centrasemi.com](http://www.centrasemi.com)



**SOT-23 CASE**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR BCX70 Series types are NPN Silicon Transistors manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for general purpose switching and amplifier applications.

**MARKING CODES:** BCX70G: AG  
BCX70H: AH  
BCX70J: AJ  
BCX70K: AK

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Collector-Base Voltage  
Collector-Emitter Voltage  
Emitter-Base Voltage  
Continuous Collector Current  
Peak Collector Current  
Peak Base Current  
Power Dissipation  
Operating and Storage Junction Temperature  
Thermal Resistance

SYMBOL		UNITS
$V_{CB0}$	45	V
$V_{CEO}$	45	V
$V_{EBO}$	5.0	V
$I_C$	100	mA
$I_{CM}$	200	mA
$I_{BM}$	200	mA
$P_D$	350	mW
$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$
$\theta_{JA}$	357	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
$I_{CBO}$	$V_{CB}=45\text{V}$			20	nA
$I_{CEO}$	$V_{CB}=45\text{V}, T_A=150^\circ\text{C}$			20	$\mu\text{A}$
$I_{EBO}$	$V_{EB}=4.0\text{V}$			20	nA
$BV_{CBO}$	$I_C=10\mu\text{A}$	45			V
$BV_{CEO}$	$I_C=10\text{mA}$	45			V
$BV_{EBO}$	$I_E=1.0\mu\text{A}$	5.0			V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=250\mu\text{A}$	0.05		0.35	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=1.25\text{mA}$	0.10		0.55	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=250\mu\text{A}$	0.60		0.85	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=1.25\text{mA}$	0.70		1.05	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=2.0\text{mA}$	0.55		0.75	V
$f_T$	$V_{CE}=5.0\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	100	250		MHz
$C_c$	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		1.7		pF
$C_e$	$V_{EB}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$		11		pF
NF	$V_{CE}=5.0\text{V}, I_C=200\mu\text{A}, R_S=2.0\text{k}\Omega, f=1.0\text{kHz}, BW=200\text{Hz}$			6.0	dB

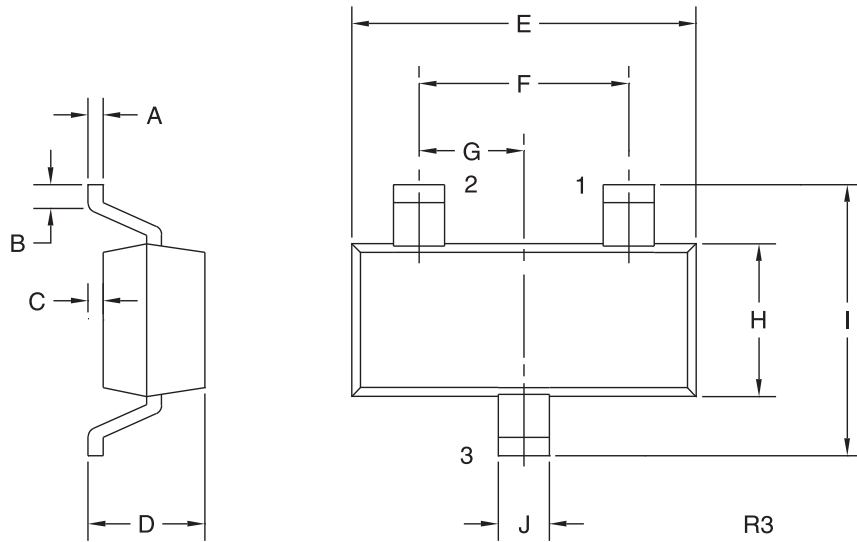
		<b>BCX70G</b>		<b>BCX70H</b>		<b>BCX70J</b>		<b>BCX70K</b>	
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=10\mu\text{A}$			40		30		100	
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=2.0\text{mA}$	120	220	180	310	250	460	380	630
$h_{FE}$	$V_{CE}=1.0\text{V}, I_C=50\text{mA}$	50		70		90		100	

R2 (20-November 2009)

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**SOT-23 CASE - MECHANICAL OUTLINE**



**LEAD CODE:**  
1) BASE  
2) EMITTER  
3) COLLECTOR

DEVICE	MARKING CODE
BCX70G	AG
BCX70H	AH
BCX70J	AJ
BCX70K	AK

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)

R2 (20-November 2009)